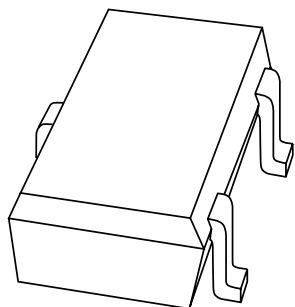


DATA SHEET



PMSS3904 NPN switching transistor

Product specification
Supersedes data of 1997 Apr 07
File under Discrete Semiconductors, SC04

1997 Sep 03

NPN switching transistor

PMSS3904

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 40 V).

APPLICATIONS

- General purpose switching and amplification
- Telephony and professional communication equipment.

DESCRIPTION

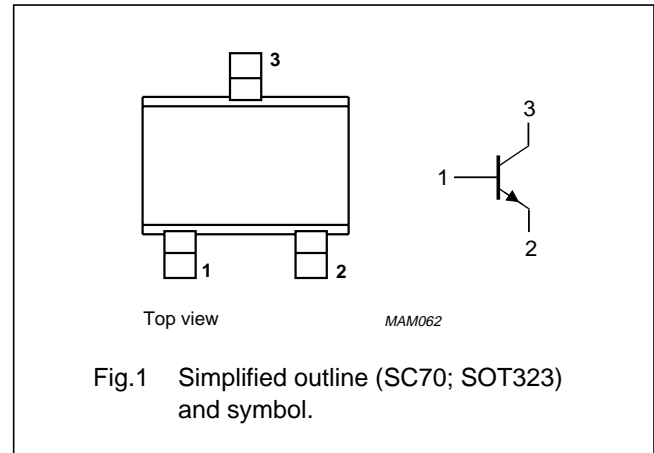
NPN switching transistor in an SC70; SOT323 plastic package. PNP complement: PMSS3906.

MARKING CODE

TYPE NUMBER	MARKING CODE
PMSS3904	t04

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	60	V
V_{CEO}	collector-emitter voltage	open base	–	40	V
I_C	collector current		–	100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$	–	200	mW
h_{FE}	DC current gain	$I_C = 10\text{ mA}; V_{CE} = 1\text{ V}$	100	300	
f_T	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 20\text{ V}; f = 100\text{ MHz}$	180	–	MHz
t_{off}	turn-off time	$I_{Con} = 10\text{ mA}; I_{Bon} = 1\text{ mA}; I_{Boff} = -1\text{ mA}$	–	1200	ns

NPN switching transistor

PMSS3904

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	60	V
V_{CEO}	collector-emitter voltage	open base	–	40	V
V_{EBO}	emitter-base voltage	open collector	–	6	V
I_C	collector current (DC)		–	100	mA
I_{CM}	peak collector current		–	200	mA
I_{BM}	peak base current		–	200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	–	200	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	625	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

NPN switching transistor

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CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 30\text{ V}$	–	50	nA
		$I_E = 0; V_{CB} = 30\text{ V}; T_j = 150\text{ }^{\circ}\text{C}$	–	10	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	50	nA
h_{FE}	DC current gain	$V_{CE} = 1\text{ V}$; see Fig.2			
		$I_C = 0.1\text{ mA}$	40	–	
		$I_C = 1\text{ mA}$	70	–	
		$I_C = 10\text{ mA}$	100	300	
		$I_C = 50\text{ mA}$; note 1	60	–	
		$I_C = 100\text{ mA}$; note 1	30	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 1\text{ mA}$	–	200	mV
		$I_C = 50\text{ mA}; I_B = 5\text{ mA}$; note 1	–	300	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 1\text{ mA}$	650	850	mV
		$I_C = 50\text{ mA}; I_B = 5\text{ mA}$; note 1	–	950	mV
C_c	collector capacitance	$I_E = i_e = 0; V_{CB} = 5\text{ V}; f = 1\text{ MHz}$	–	4	pF
C_e	emitter capacitance	$I_C = i_c = 0; V_{EB} = 0.5\text{ V}; f = 1\text{ MHz}$	–	12	pF
f_T	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 20\text{ V}; f = 100\text{ MHz}$	180	–	MHz
F	noise figure	$I_C = 100\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; R_S = 1\text{ k}\Omega$ $f = 10\text{ Hz to }15.7\text{ KHz}$	–	5	dB
Switching times (between 10% and 90% levels) see Fig.3					
t_{on}	turn-on time	$I_{Con} = 10\text{ mA}; I_{Bon} = 1\text{ mA}; I_{Boff} = -1\text{ mA};$ $V_{CC} = 3\text{ V}; V_{BB} = -1.9\text{ V}$	–	110	ns
t_d	delay time		–	50	ns
t_r	rise time		–	60	ns
t_{off}	turn-off time		–	1200	ns
t_s	storage time		–	1000	ns
t_f	fall time		–	200	ns

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

NPN switching transistor

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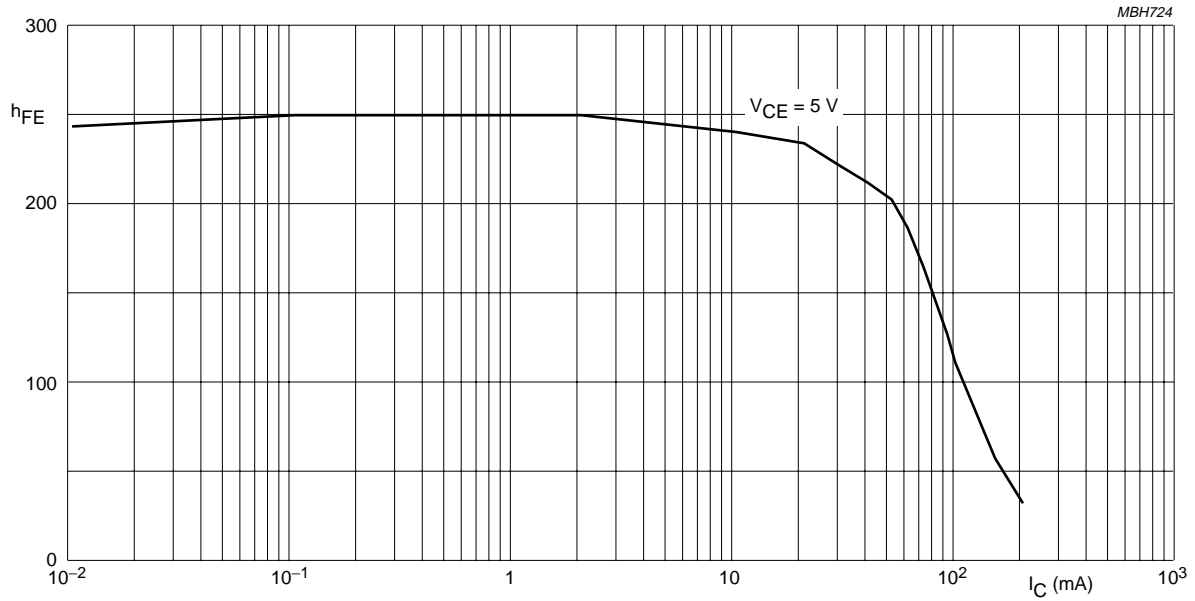
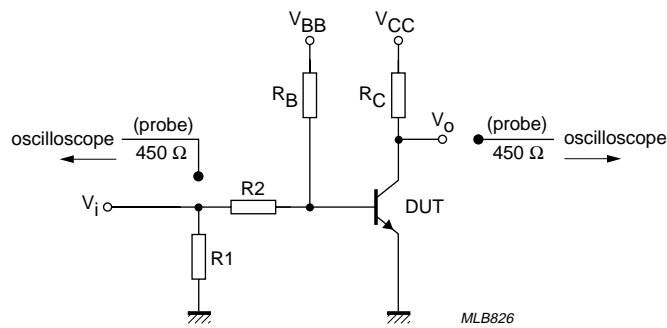


Fig.2 DC gain current; typical values.



$V_i = 5\text{ V}$; $T = 500\ \mu\text{s}$; $t_p = 10\ \mu\text{s}$; $t_r = t_f \leq 3\ \text{ns}$.
 $R_1 = 56\ \Omega$; $R_2 = 2.5\ \text{k}\Omega$; $R_B = 3.9\ \text{k}\Omega$; $R_C = 270\ \Omega$.
 Oscilloscope: input impedance $Z_i = 50\ \Omega$.

Fig.3 Test circuit for switching times.

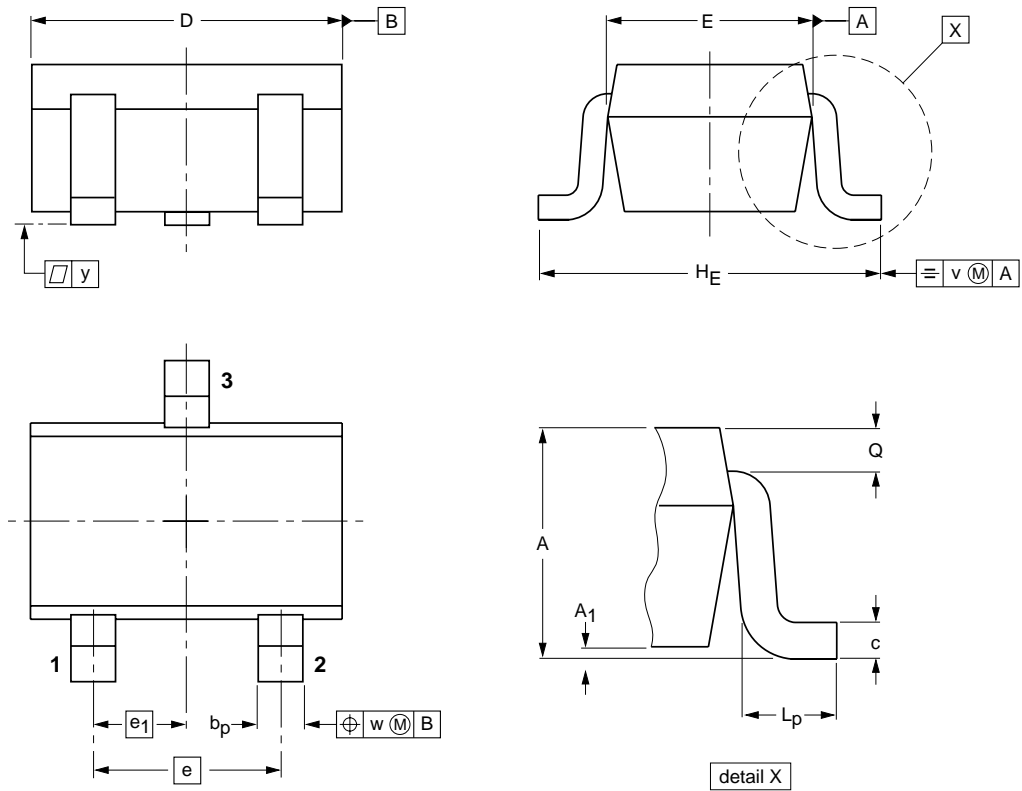
NPN switching transistor

PMSS3904

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT323			SC-70			97-02-28

NPN switching transistor

PMSS3904

DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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